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FDS6680A

## Single N-Channel, Logic Level, PowerTrench® MOSFET

General Description

This N-Channel Logic Level MOSFET is produced using Fairchild Semiconductor's advanced Power Trench process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

These devices are well suited for low voltage and battery powered applications where low in-line power loss and fast switching are required.

Features

- 12.5 A, 30 V $R_{DS(ON)}$ = 9.5 mΩ @ V_{GS} = 10 V
  $R_{DS(ON)}$ = 13 mΩ @ V_{GS} = 4.5 V

- Ultra-low gate charge

- High performance trench technology for extremely low $R_{DS(ON)}$

- High power and current handling capability

SO-8

Pin 1
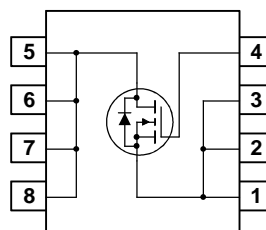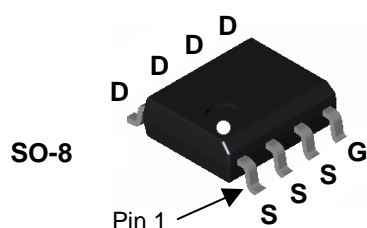
Absolute Maximum Ratings T_A=25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	
I_D	Drain Current – Continuous	(Note 1a)	12.5	A
	– Pulsed		50	
P_D	Power Dissipation for Single Operation	(Note 1a)	2.5	W
		(Note 1b)	1.2	
		(Note 1c)	1.0	
T_J, T_{STG}	Operating and Storage Junction Temperature Range		−55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction-to-Case	(Note 1a)	50	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	(Note 1)	25	

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
FDS6680A	FDS6680A	13''	12mm	2500 units

Electrical Characteristics

$T_A = 25°C$ unless otherwise noted

| Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain–Source Breakdown Voltage	$V_{GS} = 0$ V, $I_D = 250$ µA	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250$ µA, Referenced to 25°C		25		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24$ V, $V_{GS} = 0$ V			1	µA
		$V_{DS} = 24$ V, $V_{GS} = 0$ V, $T_J=55°C$			10	µA
I_{GSS}	Gate–Body Leakage	$V_{GS} = \pm20$ V, $V_{DS} = 0$ V			±100	nA
On Characteristics (Note 2)						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 250$ µA	1	2	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250$ µA, Referenced to 25°C		−4.9		mV/°C
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = 10$ V, $I_D = 12.5$ A		7.8	9.5	mΩ
		$V_{GS} = 4.5$ V, $I_D = 10.5$ A		9.9	13	
		$V_{GS} = 10$ V, $I_D = 12.5$ A, $T_J=125°C$		11.0	15	
$I_{D(on)}$	On–State Drain Current	$V_{GS} = 10$ V, $V_{DS} = 5$ V	25			A
g_{FS}	Forward Transconductance	$V_{DS} = 15$ V, $I_D = 12.5$ A		64		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 15$ V, $V_{GS} = 0$ V, f = 1.0 MHz		1620		pF
C_{oss}	Output Capacitance			380		pF
C_{rss}	Reverse Transfer Capacitance			160		pF
R_G	Gate Resistance	$V_{GS} = 15$ mV, f = 1.0 MHz		1.3		Ω
Switching Characteristics (Note 2)						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = 15$ V, $I_D = 1$ A, $V_{GS} = 10$ V, $R_{GEN} = 6$ Ω		10	19	ns
t_r	Turn–On Rise Time			5	10	ns
$t_{d(off)}$	Turn–Off Delay Time			27	43	ns
t_f	Turn–Off Fall Time			15	27	ns
Q_g	Total Gate Charge	$V_{DS} = 15$ V, $I_D = 12.5$ A, $V_{GS} = 5$ V		16	23	nC
Q_{gs}	Gate–Source Charge			5		nC
Q_{gd}	Gate–Drain Charge			5.8		nC
Drain–Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain–Source Diode Forward Current				2.1	A
V_{SD}	Drain–Source Diode Forward Voltage	$V_{GS} = 0$ V, $I_S = 2.1$ A (Note 2)		0.73	1.2	V
t_{rr}	Diode Reverse Recovery Time	$I_F = 12.5$ A, $d_{iF}/d_t = 100$ A/µs		28		ns
Q_{rr}	Diode Reverse Recovery Charge			18		nC

Notes:

1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.
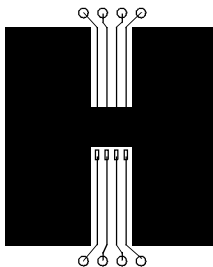
a) 50°C/W when mounted on a 1in^2 pad of 2 oz copper
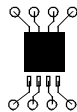
b) 105°C/W when mounted on a .04 in^2 pad of 2 oz copper
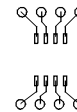
c) 125°C/W when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

Typical Characteristics
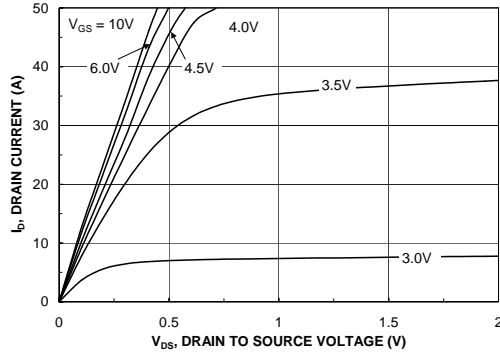
Figure 1. On-Region Characteristics.
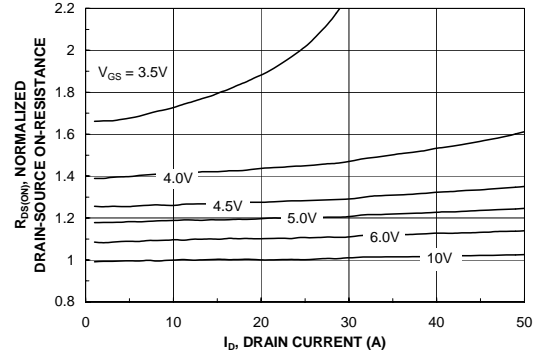
Figure 2. On-Resistance Variation with
Drain Current and Gate Voltage.
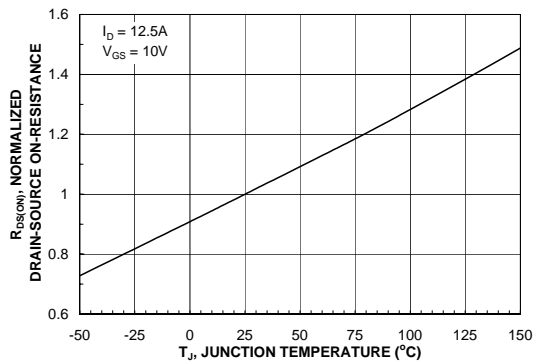
Figure 3. On-Resist ance Variation with
Temperature.
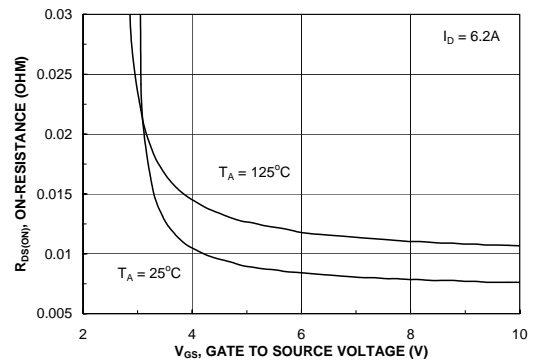
Figure 4. On-Resistance Variation with
Gate-to-Source Voltage.
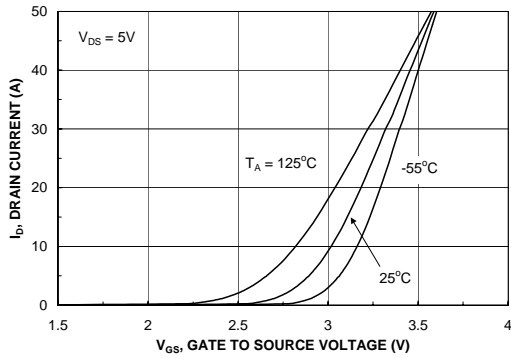
Figure 5. Transfer Characteristics.
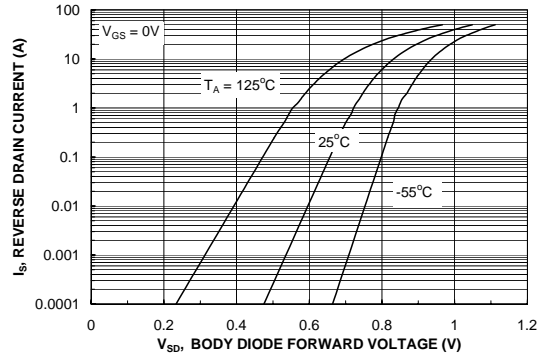
Figure 6. Body Diode Forward Voltage Variation
with Source Current and Temperature.

Typical Characteristics
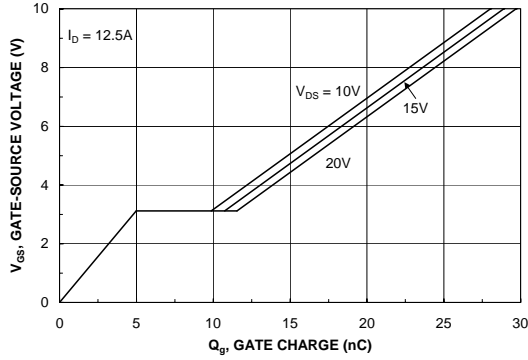
Figure 7. Gate Charge Characteristics.
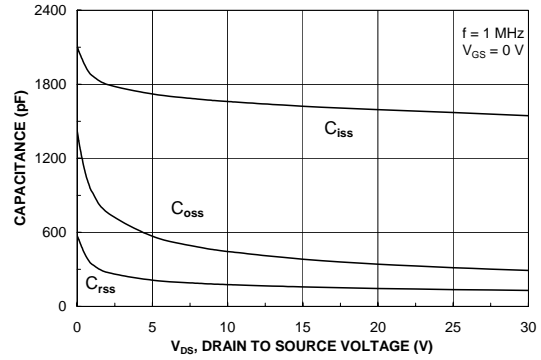
Figure 8. Capacitance Characteristics.
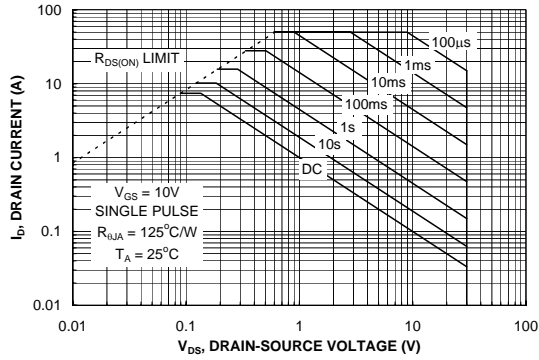
Figure 9. Maximum Safe Operating Area.
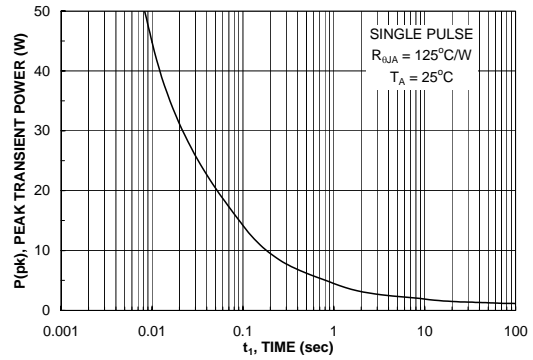
Figure 10. Single Pulse Maximum Power Dissipation.

$$R_{\theta JA}(t) = r(t) * R_{\theta JA}$$
$$R_{\theta JA} = 125^{o}C/W$$
$$T_J - T_A = P * R_{\theta JA}(t)$$
Duty Cycle, D = t_1 / t_2
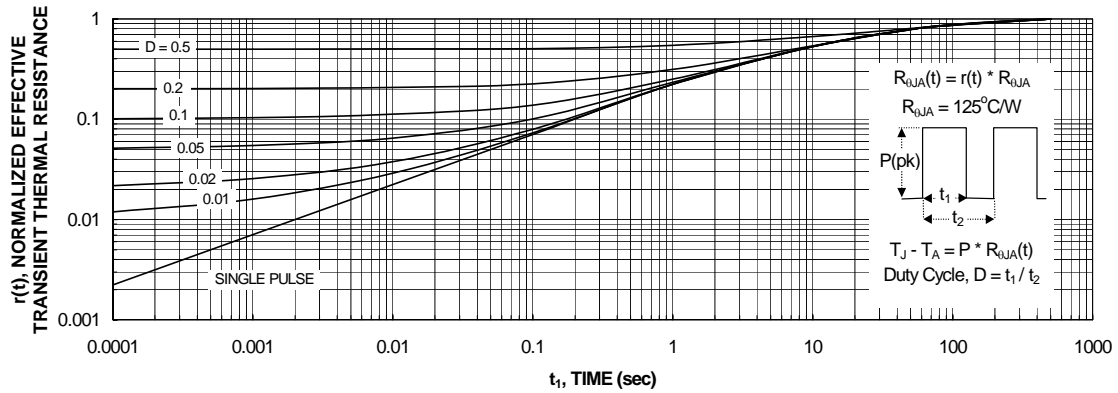
Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.
Transient thermal response will change depending on the circuit board design.

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